International
IOR Rectifier

PD-94015

IRF5803

HEXFET® Power MOSFET

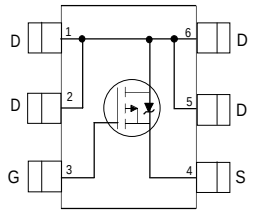
- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Low Gate Charge

V_{DSS}	$R_{DS(on)}$ max (mΩ)	I_D
-40V	112@V_{GS} = -10V	-3.4A
	190@V_{GS} = -4.5V	-2.7A

Description

These P-channel HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications.

The TSOP-6 package with its customized leadframe produces a HEXFET® power MOSFET with $R_{DS(on)}$ 60% less than a similar size SOT-23. This package is ideal for applications where printed circuit board space is at a premium. It's unique thermal design and $R_{DS(on)}$ reduction enables a current-handling increase of nearly 300% compared to the SOT-23.



Top View


TSOP-6

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-40	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ -10V	-3.4	A
I_D @ T_A= 70°C	Continuous Drain Current, V_{GS} @ -10V	-2.7	
I_{DM}	Pulsed Drain Current ①	-27	
P_D @T_A = 25°C	Power Dissipation ③	2.0	W
P_D @T_A = 70°C	Power Dissipation ③	1.3	
	Linear Derating Factor	16	mW/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	62.5	°C/W

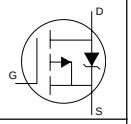
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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-40	—	—	V	V_{GS} = 0V, I_D = -250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.03	—	V/°C	Reference to 25°C, I_D = -1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	112	mΩ	V_{GS} = -10V, I_D = -3.4 ②
		—	—	190		V_{GS} = -4.5V, I_D = -2.7A ②
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	-3.0	V	V_{DS} = V_{GS}, I_D = -250µA
g_{fs}	Forward Transconductance	4.0	—	—	S	V_{DS} = -10V, I_D = -3.4A
I_{DSS}	Drain-to-Source Leakage Current	—	—	-10	µA	V_{DS} = -32V, V_{GS} = 0V
		—	—	-25		V_{DS} = -32V, V_{GS} = 0V, T_J = 70°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V_{GS} = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V_{GS} = 20V
Q_g	Total Gate Charge	—	25	37	nC	I_D = -3.4A
Q_{gs}	Gate-to-Source Charge	—	4.5	6.8		V_{DS} = -20V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	3.5	5.3		V_{GS} = -10V
$t_{d(on)}$	Turn-On Delay Time	—	43	—	ns	V_{DD} = -20V ②
t_r	Rise Time	—	550	—		I_D = -1.0A
$t_{d(off)}$	Turn-Off Delay Time	—	88	—		R_G = 6.0Ω
t_f	Fall Time	—	50	—		V_{GS} = -10V
C_{iss}	Input Capacitance	—	1110	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	93	—		V_{DS} = -25V
C_{rss}	Reverse Transfer Capacitance	—	73	—		f = 100kHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-2.0	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-27		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	T_J = 25°C, I_S = -2.0A, V_{GS} = 0V ②
t_{rr}	Reverse Recovery Time	—	27	40	ns	T_J = 25°C, I_F = -2.0A
Q_{rr}	Reverse Recovery Charge	—	34	50	nC	di/dt = -100A/µs ②



Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width ≤ 400µs; duty cycle ≤ 2%.

③ Surface mounted on 1 in square Cu board

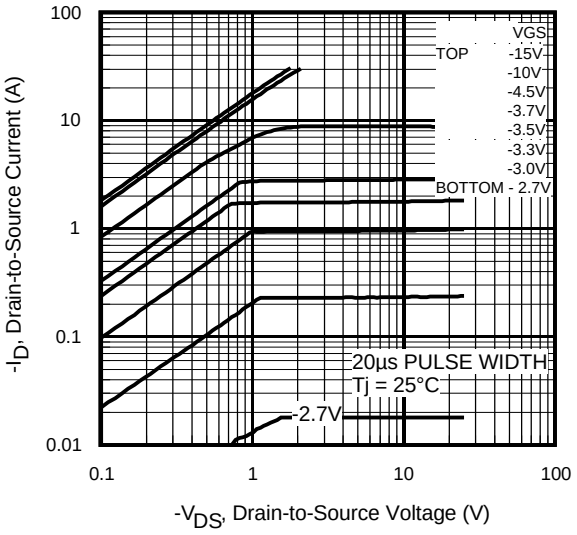


Fig 1. Typical Output Characteristics

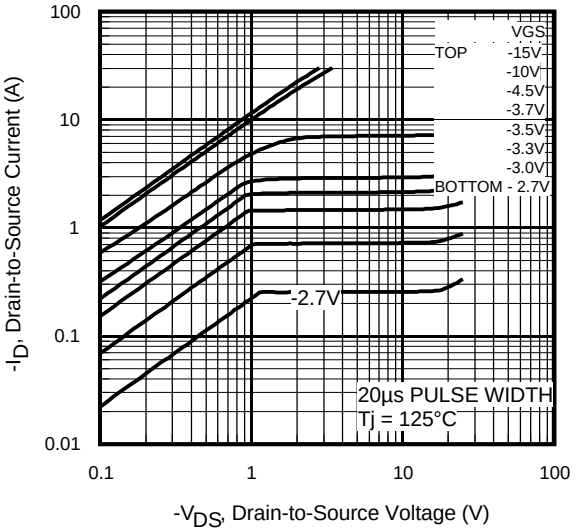


Fig 2. Typical Output Characteristics

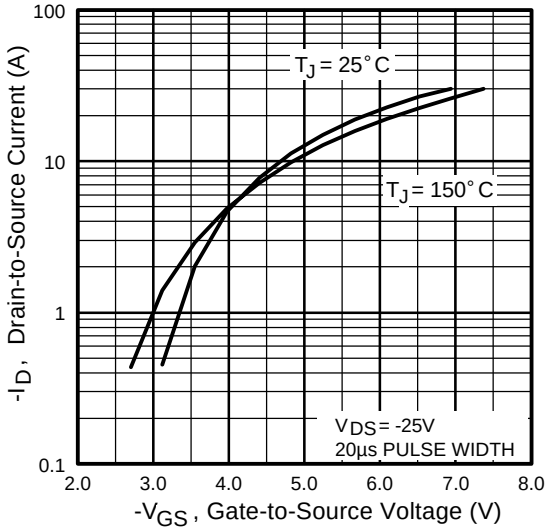


Fig 3. Typical Transfer Characteristics

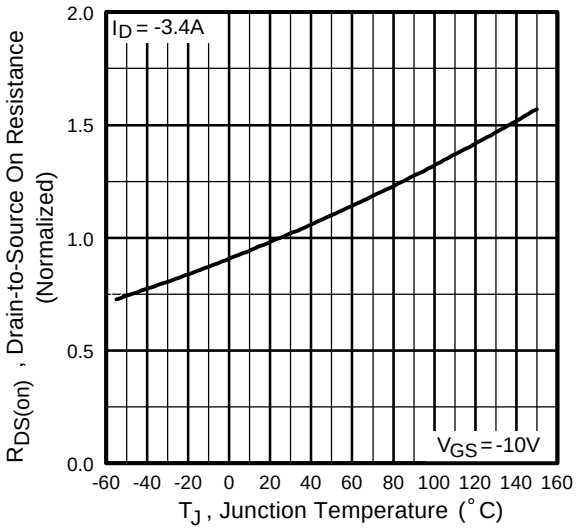


Fig 4. Normalized On-Resistance Vs. Temperature

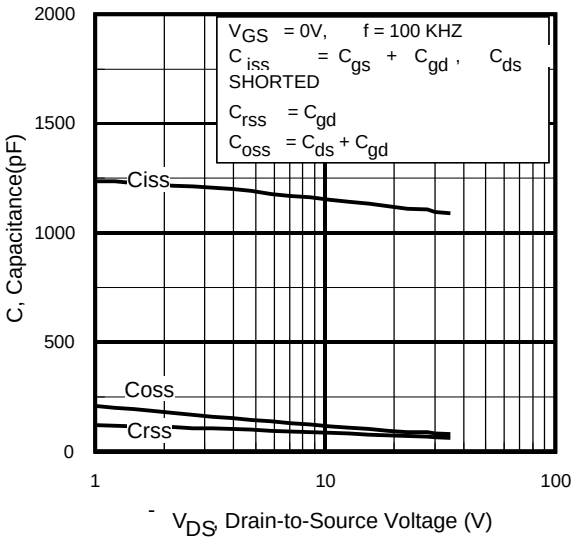


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

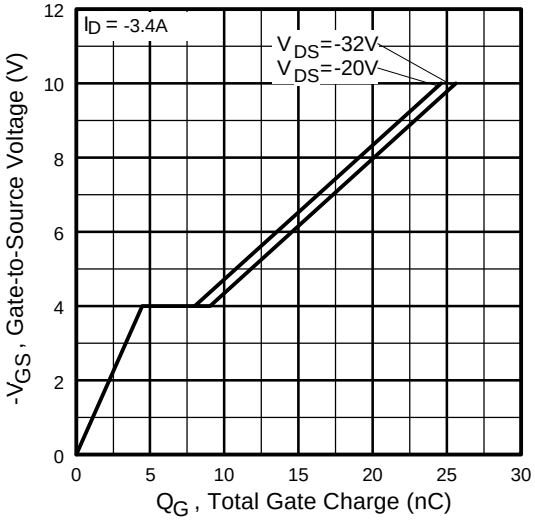


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

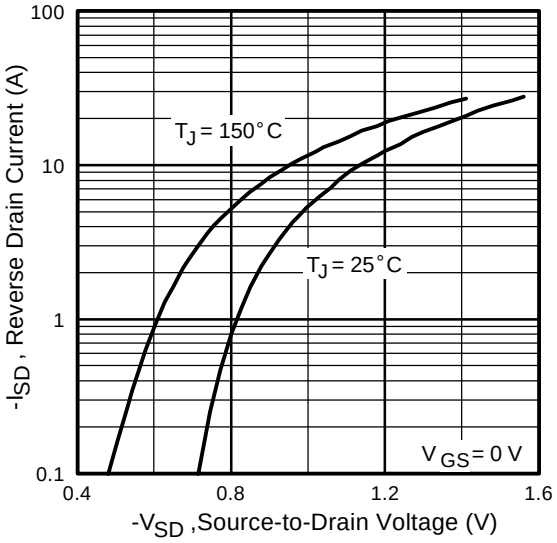


Fig 7. Typical Source-Drain Diode Forward Voltage

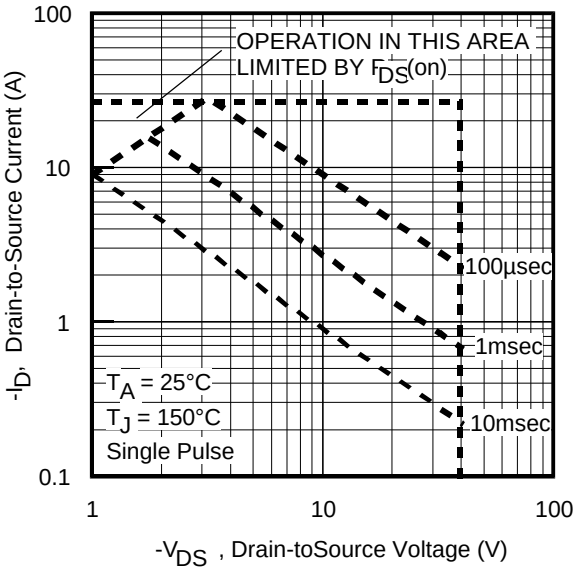


Fig 8. Maximum Safe Operating Area

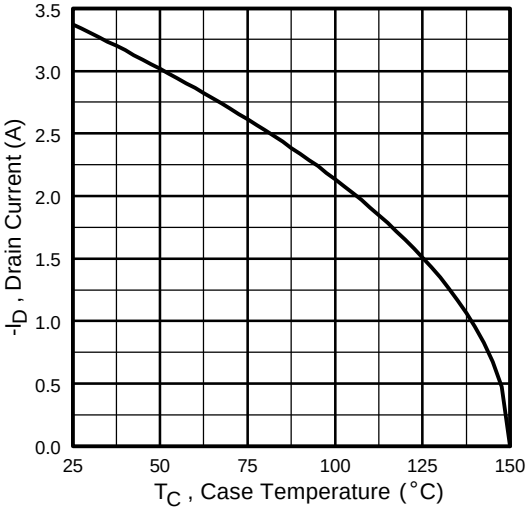


Fig 9. Maximum Drain Current Vs. Case Temperature

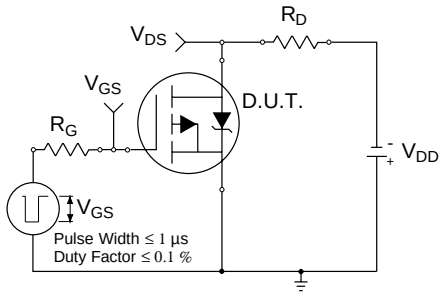


Fig 10a. Switching Time Test Circuit

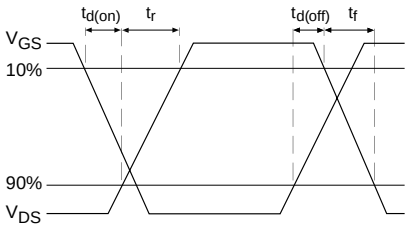


Fig 10b. Switching Time Waveforms

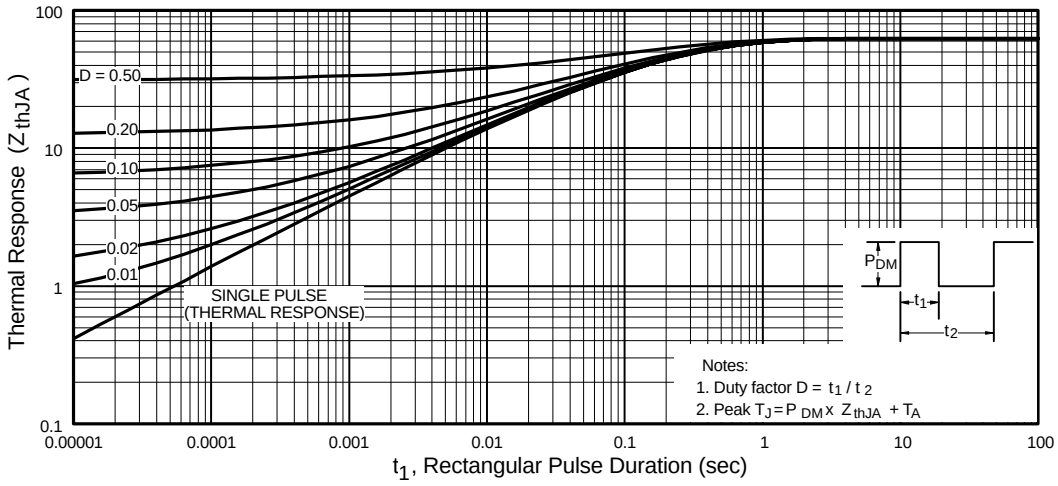


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

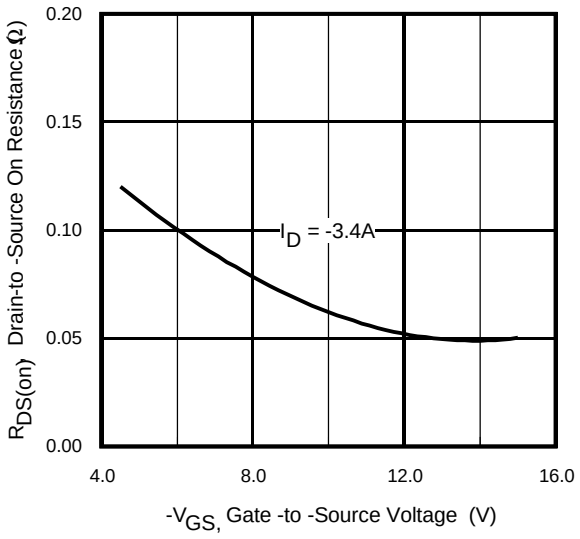


Fig 12. Typical On-Resistance Vs. Gate Voltage

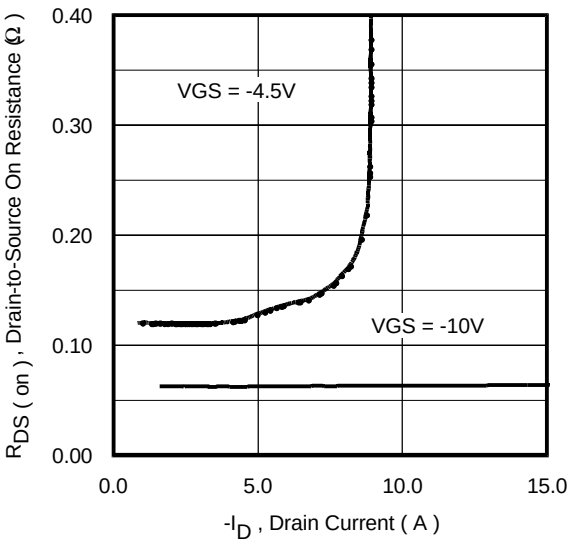


Fig 13. Typical On-Resistance Vs. Drain Current

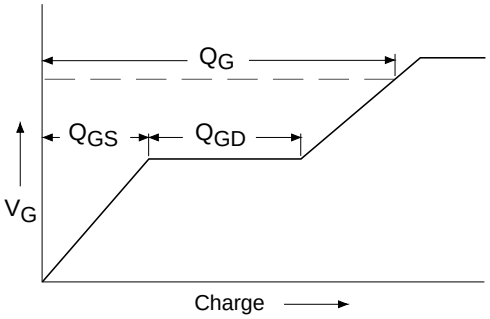


Fig 14a. Basic Gate Charge Waveform

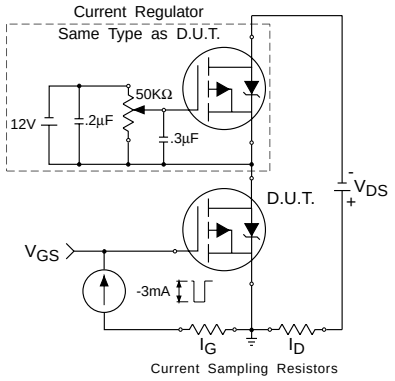


Fig 14b. Gate Charge Test Circuit

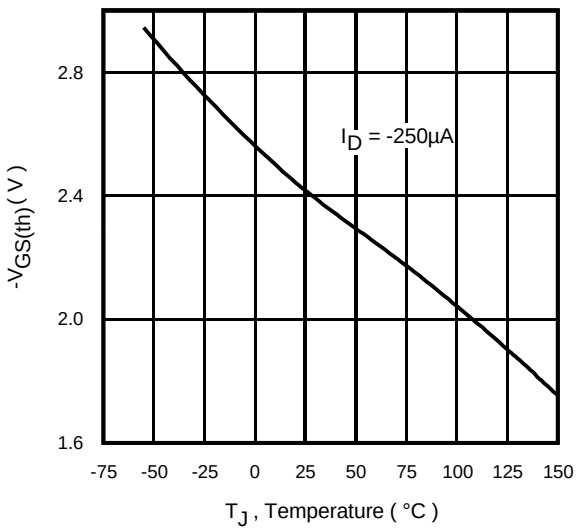


Fig 15. Typical Threshold Voltage Vs. Junction Temperature

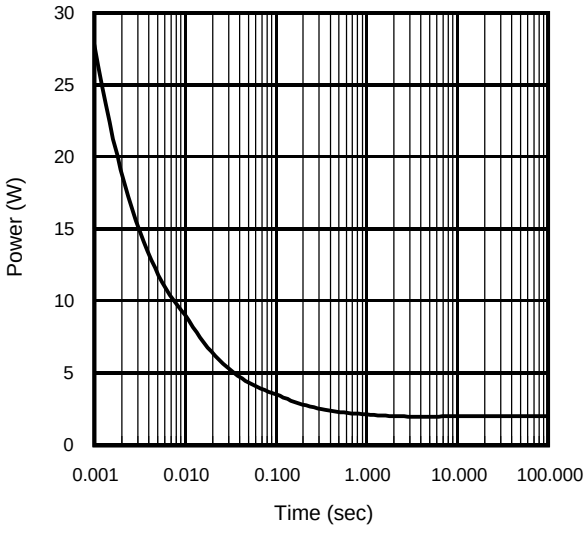
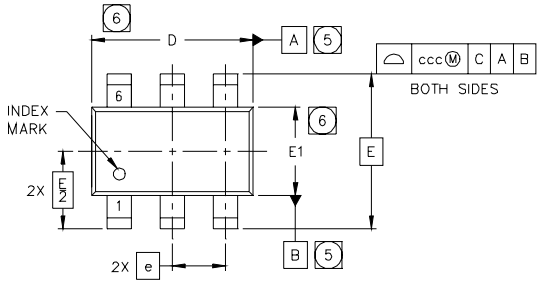
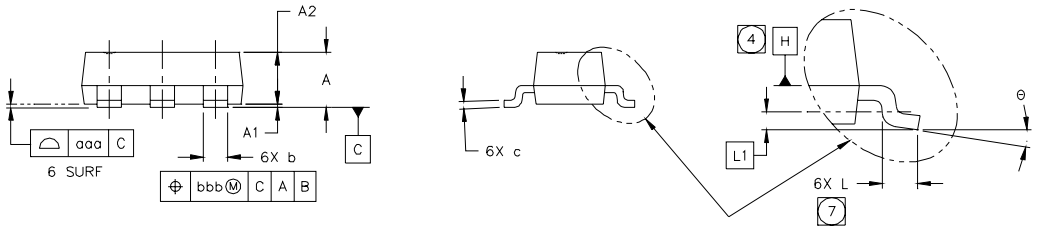


Fig 16. Typical Power Vs. Time

TSOP-6 Package Outline

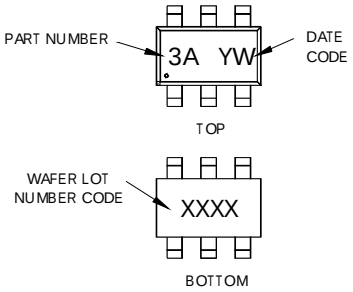


SYMBOL	MO-193AA DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	.0433
A1	0.01	---	0.10	.0004	---	.0039
A2	0.80	0.90	1.00	.0315	.0354	.0393
b	0.25	---	0.50	.0099	---	.0196
c	0.10	---	0.26	.004	---	.010
D	2.90	3.00	3.10	.115	.118	.122
E	2.75 BSC			.108 BSC		
E1	1.30	1.50	1.70	.052	.059	.066
e	1.00 BSC			.039 BSC		
L	0.20	0.40	0.60	.0079	.0157	.0236
L1	0.30 BSC			.0118 BSC		
θ	0°	---	8°	0°	---	8°
aaa	0.10			.004		
bbb	0.15			.006		
ccc	0.25			.010		



TSOP-6 Part Marking Information

EXAMPLE: THIS IS AN SI3443DV



PART NUMBER CODE REFERENCE:

3A = SI3443DV
3B = IRF5800
3C = IRF5850
3D = IRF5851
3E = IRF5852
3I = IRF5805
3J = IRF5806

DATE CODE EXAMPLES:

YWW = 9603 = 6C
YWW = 9632 = FF

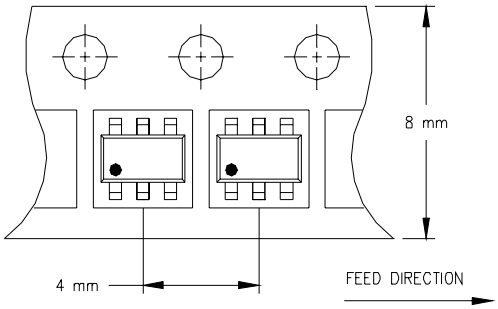
WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

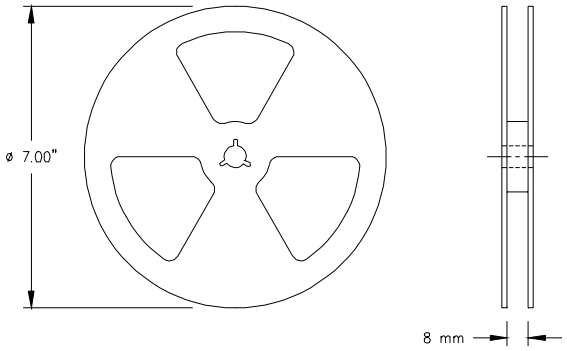
WW = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

TSOP-6 Tape & Reel Information



NOTES:
1. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:
1. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
This product has been designed and qualified for the consumer market.
Qualification Standards can be found on IR's Web site.

International
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